

AMENDMENTS TO THE CLAIMS

Please cancel Claims 25-29 and 33-39.

Please amend Claims 30 and 31 as follows:

1- 24. (Withdrawn)

25 - 29. (Cancelled)

30. (Currently Amended) A method according to Claim 25 for manufacturing a semiconductor film comprising the steps of:

preparing a first member including a semiconductor substrate, a semiconductor layer whose resistivity is higher than a resistivity of the semiconductor substrate, and a separation layer provided between the semiconductor substrate and the semiconductor layer; and

separating the semiconductor layer from the semiconductor substrate at the separation layer by heating the first member by induction heating,

wherein said step for preparing the first member comprises a step of forming a porous silicon layer, serving as a separation layer, by anodizing a surface of a p⁺-type nonporous silicon substrate, and a step of forming a p⁻-type nonporous silicon layer on the porous silicon layer according to epitaxial growth.

31. (Currently Amended) A method according to Claim 25 for manufacturing a semiconductor film comprising the steps of:

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preparing a first member including a semiconductor substrate, a semiconductor layer whose resistivity is higher than a resistivity of the semiconductor substrate, and a separation layer provided between the semiconductor substrate and the semiconductor layer; and

separating the semiconductor layer from the semiconductor substrate at the separation layer by heating the first member by induction heating,

wherein said step for preparing the first member comprises a step of forming a p⁻-type silicon layer on a p⁺-type silicon substrate according to epitaxial growth, and forming an ion-implanted layer, serving as a separation layer, except for a p⁻-type silicon layer where ions are not implanted on a surface thereof, by implanting at least one type of ions selected from hydrogen, nitrogen and helium to a predetermined depth from a surface of the p⁻-type silicon layer.

32. (Original) A method according to Claim 31, wherein said step of preparing the first member further comprises a step of forming a protective film on the surface of the p⁻-type silicon layer before implanting the ions.

33 - 39. (Cancelled)

40 - 58. (Withdrawn)